National Semiconductor

February 1993

CD4093BM/CD4093BC Quad 2-Input NAND Schmitt Trigger

General Description

The CD4093B consists of four Schmitt-trigger circuits. Each circuit functions as a 2-input NAND gate with Schmitt-trigger action on both inputs. The gate switches at different points for positive and negative-going signals. The difference between the positive ($V_T{}^{+}$) and the negative voltage ($V_T{}^{-}$) is defined as hysteresis voltage (V_H).

All outputs have equal source and sink currents and conform to standard B-series output drive (see Static Electrical Characteristics).

Features

- Wide supply voltage range 3.0V to 15V
- Schmitt-trigger on each input with no external components
- Noise immunity greater than 50%
- Equal source and sink currents
- No limit on input rise and fall time
- Standard B-series output drive
- Hysteresis voltage (any input) $T_A = 25°C$

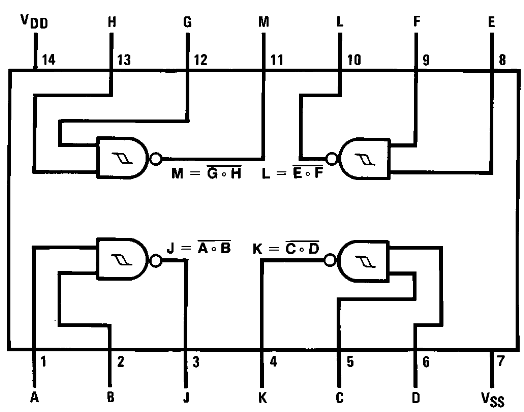
Typical	$V_{DD} = 5.0V$	$V_H = 1.5V$
	$V_{DD} = 10V$	$V_H = 2.2V$
	$V_{DD} = 15V$	$V_H = 2.7V$
Guaranteed		$V_H = 0.1\ V_{DD}$

Applications

- Wave and pulse shapers
- High-noise-environment systems
- Monostable multivibrators
- Astable multivibrators
- NAND logic

Connection Diagram

Dual-In-Line Package



TL/F/5982–1

Top View

Order Number CD4093B

RRD-B30M105/Printed in U. S. A.

Absolute Maximum Ratings (Notes 1 & 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

DC Supply Voltage (V_{DD})	-0.5 to $+18$ V_{DC}
Input Voltage (V_{IN})	-0.5 to V_{DD} $+0.5$ V_{DC}
Storage Temperature Range (T_S)	$-65°C$ to $+150°C$
Power Dissipation (P_D)	
Dual-In-Line	700 mW
Small Outline	500 mW
Lead Temperature (T_L) (Soldering, 10 seconds)	260°C

Recommended Operating Conditions (Note 2)

DC Supply Voltage (V_{DD})	3 to 15 V_{DC}
Input Voltage (V_{IN})	0 to V_{DD} V_{DC}
Operating Temperature Range (T_A)	
CD4093BM	$-55°C$ to $+125°C$
CD4093BC	$-40°C$ to $+85°C$

DC Electrical Characteristics CD4093BM (Note 2)

Symbol	Parameter	Conditions	$-55°C$		$+25°C$			$+125°C$		Units
			Min	Max	Min	Typ	Max	Min	Max	
I_{DD}	Quiescent Device Current	$V_{DD} = 5V$		0.25			0.25		7.5	μA
		$V_{DD} = 10V$		0.5			0.5		15.0	μA
		$V_{DD} = 15V$		1.0			1.0		30.0	μA
V_{OL}	Low Level Output Voltage	$V_{IN} = V_{DD}$, $\lvert I_O \rvert < 1$ μA								
		$V_{DD} = 5V$		0.05		0	0.05		0.05	V
		$V_{DD} = 10V$		0.05		0	0.05		0.05	V
		$V_{DD} = 15V$		0.05		0	0.05		0.05	V
V_{OH}	High Level Output Voltage	$V_{IN} = V_{SS}$, $\lvert I_O \rvert < 1$ μA								
		$V_{DD} = 5V$	4.95		4.95	5		4.95		V
		$V_{DD} = 10V$	9.95		9.95	10		9.95		V
		$V_{DD} = 15V$	14.95		14.95	15		14.95		V
V_T^-	Negative-Going Threshold Voltage (Any Input)	$\lvert I_O \rvert < 1$ μA								
		$V_{DD} = 5V$, $V_O = 4.5V$	1.3	2.25	1.5	1.8	2.25	1.5	2.3	V
		$V_{DD} = 10V$, $V_O = 9V$	2.85	4.5	3.0	4.1	4.5	3.0	4.65	V
		$V_{DD} = 15V$, $V_O = 13.5V$	4.35	6.75	4.5	6.3	6.75	4.5	6.9	V
V_T^+	Positive-Going Threshold Voltage (Any Input)	$\lvert I_O \rvert < 1$ μA								
		$V_{DD} = 5V$, $V_O = 0.5V$	2.75	3.65	2.75	3.3	3.5	2.65	3.5	V
		$V_{DD} = 10V$, $V_O = 1V$	5.5	7.15	5.5	6.2	7.0	5.35	7.0	V
		$V_{DD} = 15V$, $V_O = 1.5V$	8.25	10.65	8.25	9.0	10.5	8.1	10.5	V
V_H	Hysteresis ($V_T^+ - V_T^-$) (Any Input)	$V_{DD} = 5V$	0.5	2.35	0.5	1.5	2.0	0.35	2.0	V
		$V_{DD} = 10V$	1.0	4.30	1.0	2.2	4.0	0.70	4.0	V
		$V_{DD} = 15V$	1.5	6.30	1.5	2.7	6.0	1.20	6.0	V
I_{OL}	Low Level Output Current (Note 3)	$V_{IN} = V_{DD}$								
		$V_{DD} = 5V$, $V_O = 0.4V$	0.64		0.51	0.88		0.36		mA
		$V_{DD} = 10V$, $V_O = 0.5V$	1.6		1.3	2.25		0.9		mA
		$V_{DD} = 15V$, $V_O = 1.5V$	4.2		3.4	8.8		2.4		mA
I_{OH}	High Level Output Current (Note 3)	$V_{IN} = V_{SS}$								
		$V_{DD} = 5V$, $V_O = 4.6V$	-0.64		0.51	-0.88		-0.36		mA
		$V_{DD} = 10V$, $V_O = 9.5V$	-1.6		-1.3	-2.25		-0.9		mA
		$V_{DD} = 15V$, $V_O = 13.5V$	-4.2		-3.4	-8.8		-2.4		mA
I_{IN}	Input Current	$V_{DD} = 15V$, $V_{IN} = 0V$		-0.1		-10^{-5}	-0.1		-1.0	μA
		$V_{DD} = 15V$, $V_{IN} = 15V$		0.1		10^{-5}	0.1		1.0	μA

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed; they are not meant to imply that the devices should be operated at these limits. The table of "Recommended Operating Conditions" and "Electrical Characteristics" provides conditions for actual device operation.

Note 2: $V_{SS} = 0V$ unless otherwise specified.

Note 3: I_{OH} and I_{OL} are tested one output at a time.

DC Electrical Characteristics CD4093BC (Note 2)

Symbol	Parameter	Conditions	−40°C		+25°C			+85°C		Units
			Min	Max	Min	Typ	Max	Min	Max	
I_{DD}	Quiescent Device Current	$V_{DD} = 5V$		1.0			1.0		7.5	μA
		$V_{DD} = 10V$		2.0			2.0		15.0	μA
		$V_{DD} = 15V$		4.0			4.0		30.0	μA
V_{OL}	Low Level Output Voltage	$V_{IN} = V_{DD}, \|I_O\| < 1\ \mu A$								
		$V_{DD} = 5V$		0.05		0	0.05		0.05	V
		$V_{DD} = 10V$		0.05		0	0.05		0.05	V
		$V_{DD} = 15V$		0.05		0	0.05		0.05	V
V_{OH}	High Level Output Voltage	$V_{IN} = V_{SS}, \|I_O\| < 1\ \mu A$								
		$V_{DD} = 5V$	4.95		4.95	5		4.95		V
		$V_{DD} = 10V$	9.95		9.95	10		9.95		V
		$V_{DD} = 15V$	14.95		14.95	15		14.95		V
V_T^-	Negative-Going Threshold Voltage (Any Input)	$\|I_O\| < 1\ \mu A$								
		$V_{DD} = 5V, V_O = 4.5V$	1.3	2.25	1.5	1.8	2.25	1.5	2.3	V
		$V_{DD} = 10V, V_O = 9V$	2.85	4.5	3.0	4.1	4.5	3.0	4.65	V
		$V_{DD} = 15V, V_O = 13.5V$	4.35	6.75	4.5	6.3	6.75	4.5	6.9	V
V_T^+	Positive-Going Threshold Voltage (Any Input)	$\|I_O\| < 1\ \mu A$								
		$V_{DD} = 5V, V_O = 0.5V$	2.75	3.6	2.75	3.3	3.5	2.65	3.5	V
		$V_{DD} = 10V, V_O = 1V$	5.5	7.15	5.5	6.2	7.0	5.35	7.0	V
		$V_{DD} = 15V, V_O = 1.5V$	8.25	10.65	8.25	9.0	10.5	8.1	10.5	V
V_H	Hysteresis ($V_T^+ - V_T^-$) (Any Input)	$V_{DD} = 5V$	0.5	2.35	0.5	1.5	2.0	0.35	2.0	V
		$V_{DD} = 10V$	1.0	4.3	1.0	2.2	4.0	0.70	4.0	V
		$V_{DD} = 15V$	1.5	6.3	1.5	2.7	6.0	1.20	6.0	V
I_{OL}	Low Level Output Current (Note 3)	$V_{IN} = V_{DD}$								
		$V_{DD} = 5V, V_O = 0.4V$	0.52		0.44	0.88		0.36		mA
		$V_{DD} = 10V, V_O = 0.5V$	1.3		1.1	2.25		0.9		mA
		$V_{DD} = 15V, V_O = 1.5V$	3.6		3.0	8.8		2.4		mA
I_{OH}	High Level Output Current (Note 3)	$V_{IN} = V_{SS}$								
		$V_{DD} = 5V, V_O = 4.6V$	−0.52		0.44	−0.88		−0.36		mA
		$V_{DD} = 10V, V_O = 9.5V$	−1.3		−1.1	−2.25		−0.9		mA
		$V_{DD} = 15V, V_O = 13.5V$	−3.6		−3.0	−8.8		−2.4		mA
I_{IN}	Input Current	$V_{DD} = 15V, V_{IN} = 0V$		−0.3		-10^{-5}	−0.3		−1.0	μA
		$V_{DD} = 15V, V_{IN} = 15V$		0.3		10^{-5}	0.3		1.0	μA

AC Electrical Characteristics*

$T_A = 25°C$, $C_L = 50$ pF, $R_L = 200k$, Input t_r, $t_f = 20$ ns, unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ	Max	Units
t_{PHL}, t_{PLH}	Propagation Delay Time	$V_{DD} = 5V$		300	450	ns
		$V_{DD} = 10V$		120	210	ns
		$V_{DD} = 15V$		80	160	ns
t_{THL}, t_{TLH}	Transition Time	$V_{DD} = 5V$		90	145	ns
		$V_{DD} = 10V$		50	75	ns
		$V_{DD} = 15V$		40	60	ns
C_{IN}	Input Capacitance	(Any Input)		5.0	7.5	pF
C_{PD}	Power Dissipation Capacitance	(Per Gate)		24		pF

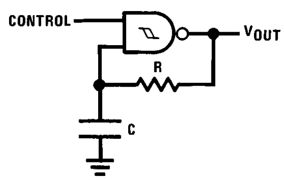
*AC Parameters are guaranteed by DC correlated testing.

Note 2: $V_{SS} = 0V$ unless otherwise specified.

Note 3: I_{OH} and I_{OL} are tested one output at a time.

Typical Applications

Gated Oscillator



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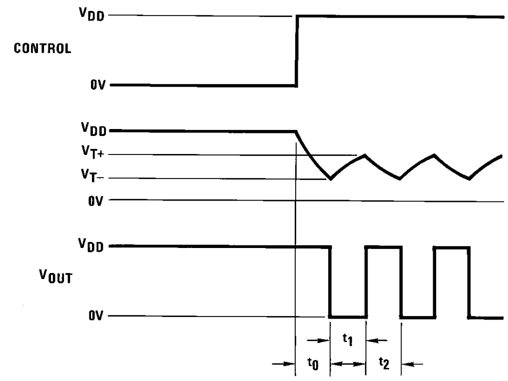

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Assume $t_1 + t_2 >> t_{PHL} + t_{PLH}$ then:

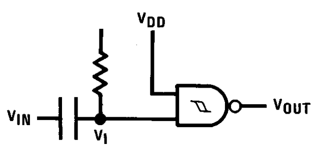
$t_0 = RC\ \ell n\ [V_{DD}/V_T^-]$

$t_1 = RC\ \ell n\ [(V_{DD} - V_T^-)/(V_{DD} - V_T^+)]$

$t_2 = RC\ \ell n\ [V_T^+/V_T^-]$

$$f = \frac{1}{t_1 + t_2} = \frac{1}{RC\ \ell n \frac{(V_T^+)\ (V_{DD} - V_T^-)}{(V_T^-)(V_{DD} - V_T^+)}}$$

Gated One-Shot



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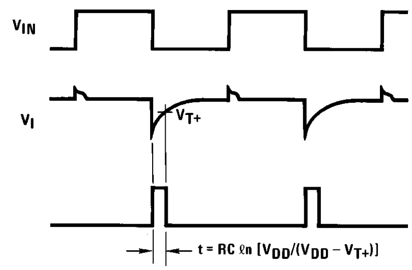

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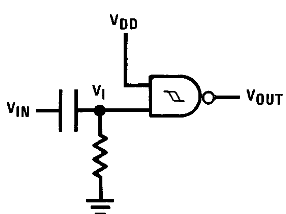
(a) Negative-Edge Triggered



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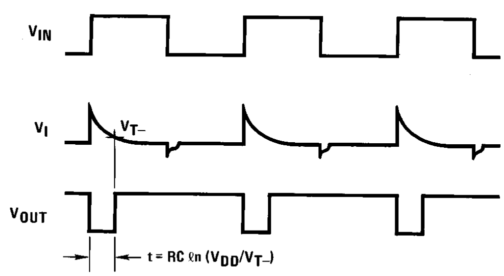

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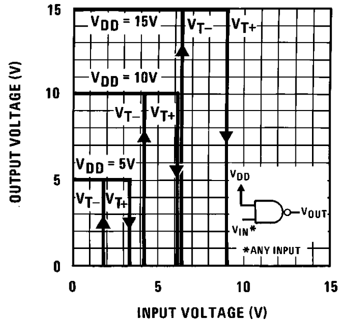
(b) Positive-Edge Triggered

Typical Performance Characteristics

Typical Transfer Characteristics



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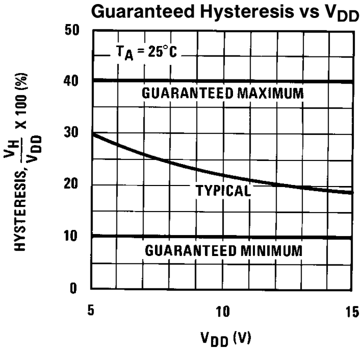
Guaranteed Hysteresis vs V_{DD}



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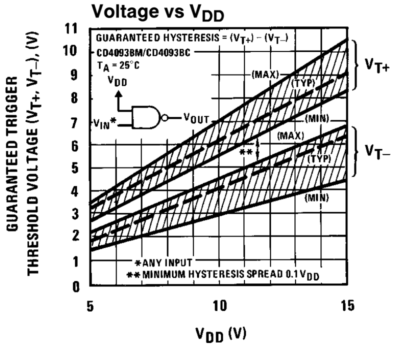
Guaranteed Trigger Threshold Voltage vs V_{DD}



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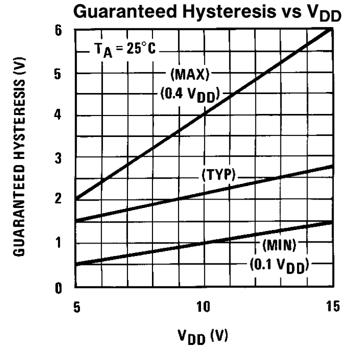
Guaranteed Hysteresis vs V_{DD}



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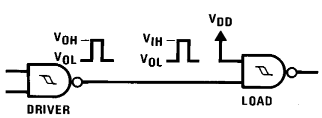
Input and Output Characteristics



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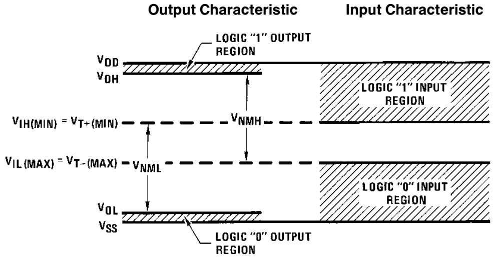
Output Characteristic **Input Characteristic**



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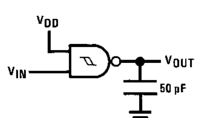
$V_{NML} = V_{IH(MIN)} - V_{OL} \cong V_{IH(MIN)} = V_{T^+(MIN)}$

$V_{NMH} = V_{OH} - V_{IL(MAX)} \cong V_{DD} - V_{IL(MAX)} = V_{DD} - V_{T^-(MAX)}$

AC Test Circuits and Switching Time Waveforms



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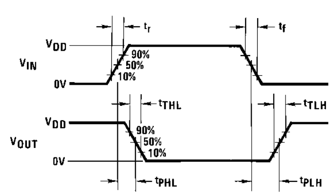

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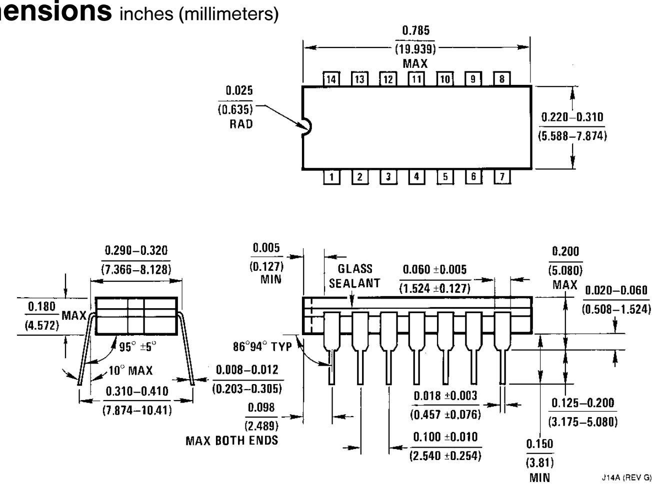
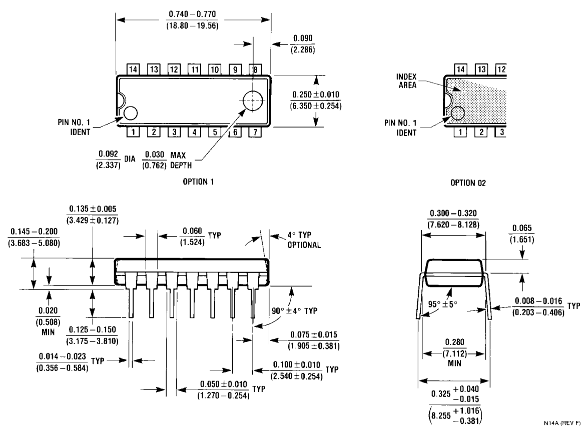
Physical Dimensions inches (millimeters)



Ceramic Dual-In-Line Package (J)
Order Number CD4093BMJ or CD4093BCJ
NS Package Number J14A



Molded Dual-In-Line Package (N)
Order Number CD4093BM or CD4093BCN
NS Package Number N14A

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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